# **PNA1601M** (PN166)

### Silicon planar type

For optical control systems

#### ■ Features

- High sensitivity
- Wide sspectral sensitivity characteristics, suited for detecting various kinds of LEDs
- Ultraminiature, thin side-view type package

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

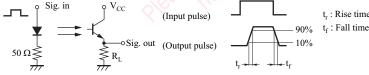
Parameter	Symbol	Rating	Unit	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	20	V	
Collector current	$I_{\rm C}$	20	mA	
Collector power dissipation *	$P_{\rm C}$	50	mW	
Operating ambient temperature	T <sub>opr</sub>	-25 to +65	°C	
Storage temperature	T <sub>stg</sub>	-30 to +85	°C	

Note) \*: The rate of electric power reduction is 1.5 mW/ $^{\circ}$ C above  $T_a = 25^{\circ}$ C.

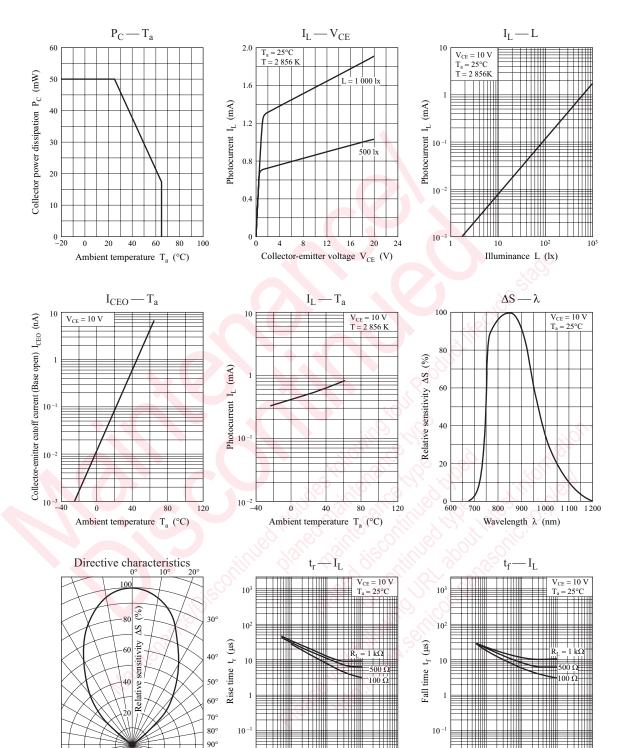
#### ■ Electrical-Optical Characteristics $T_a = 25$ °C±3°C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Sensitivity to infrared radiation *1	S <sub>IR</sub>	$V_{CE} = 10 \text{ V}, H = 15 \mu\text{W/cm}^2$	3	5	25	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 10 \text{ V}$		illi	0.2	μΑ
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_C = 10 \mu A, H = 15 \mu W/cm^2$	S XC	3	0.5	V
Peak sensitivity wavelength	$\lambda_{ ext{PD}}$	$V_{CE} = 10 \text{ V}$	11/0	850		nm
Half-power angle	θ	The angle when the sensitivity to infrared radiation is halved	7.82	35		O
Rise time *2	t <sub>r</sub>	V - 10 V I - 5 - A D - 100 O	60	4		μs
Fall time *2	$t_{\rm f}$	$V_{CC} = 10 \text{ V}, I_C = 5 \text{ mA}, R_L = 100 \Omega$		4		μs

- Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
  - 2. Spectral sensitivity characteristics: Sensitivity for wave length over 400 nm maximum sensitivity ratio is 100%.
  - 3. This device is designed by disregarding radiation.
  - 4. \*1:Source: Infrared radiation ( $\lambda = 940 \text{ nm}$ )
    - \*2: Switching time measurement circuit



Note) The part number in the parenthesis shows conventional part number.



Photocurrent I<sub>L</sub> (mA)

10 -2 10 -2

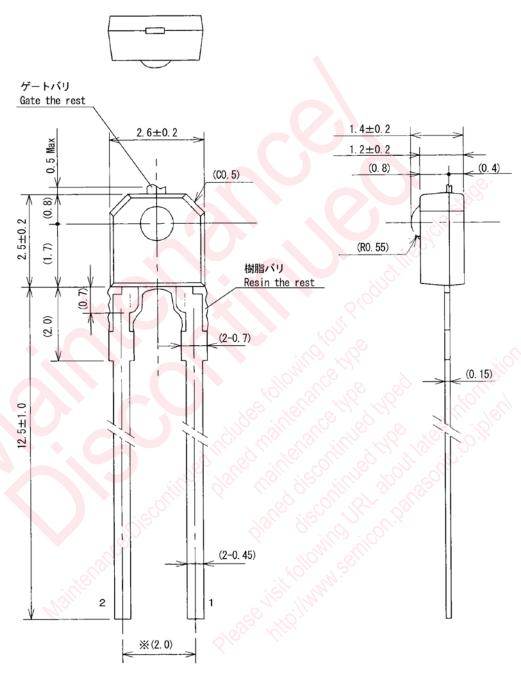
Photocurrent I<sub>L</sub> (mA)

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Panasonic PNA1601M

#### ■ Package (Unit: mm)

### LPTLSN2S0004



(注 1)※リード根元寸法とする。/(Note1)※Indicates root dimensions of lead.

- Pin name
  - 1: Collector
  - 2: Emitter

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